FEM Validation of a Single Degree of Freedom Model for Piezoelectric Energy Harvesters

Alcala, Lucia R.; Lei, Anders; Larsen, Mikkel V.; Durhuus, Døgg; Thomsen, Erik Vilain

Publication date:
2015

Document Version
Publisher's PDF, also known as Version of record

Link back to DTU Orbit

Citation (APA):

General rights
Copyright and moral rights for the publications made accessible in the public portal are retained by the authors and/or other copyright owners and it is a condition of accessing publications that users recognise and abide by the legal requirements associated with these rights.

- Users may download and print one copy of any publication from the public portal for the purpose of private study or research.
- You may not further distribute the material or use it for any profit-making activity or commercial gain
- You may freely distribute the URL identifying the publication in the public portal

If you believe that this document breaches copyright please contact us providing details, and we will remove access to the work immediately and investigate your claim.
FEM Validation of a Single Degree of Freedom Model for Piezoelectric Energy Harvesters

Lucia R. Alcala, Anders Lei, Mikkel V. Larsen, Døgg Durhuus, Erik V. Thomsen.

Ambient vibrations are present in different environments. Energy can be extracted from these sources by using piezoelectric energy harvesters, enabling these devices to obtain low-power energy.

Most ambient vibrations extend over a wide low frequency range. Therefore, the design of the cantilevers must be aimed at very low frequencies. This can be achieved by tuning the cantilever thickness and relative dimensions of the proof mass and cantilever beam. Analytical models were validated by FEM simulation methods, which allow for an optimal design.

The devices are aimed to replace low-power batteries, for that reason the total lengths of the devices should be preferable within one centimetre.

Device's optimal dimensions
The optimal relative dimensions of the proof mass and the cantilever as well as the thickness of the cantilevers are studied in order to achieve the lowest resonance frequency.

Piezoelectric material
The piezoelectric material Aluminium Nitride (AlN) is normally deposited via reactive sputtering, which is a time-consuming process. It becomes therefore important to determine how the thickness of the AlN layer affects the output power that can be harvested.

Fig. 4 shows the power versus the piezoelectric layer thickness, it can be seen that the power depends on the thickness until a certain value is reached. Beyond that value the AlN thickness does not affect the obtained power, being it constant over thicker layers.